2SC3478

Rev.E Mar.-2016

DATA SHEET

WR0<5 ṂṂĿ QSQ ӕṀч s Ⅱ ⅂ Silicon NPN transistor in a TO-92 Plastic Package.

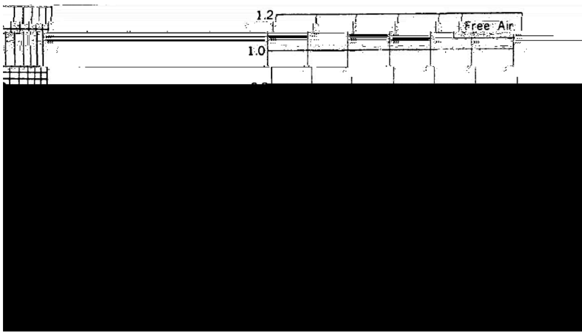
ㄨ Ͻ я ı ῷ ᶾ ┤ ớ Ḅ/љ 5VD46:9 Ӣ ´
High breakdown voltage, good h_{FE} linearity, complementary to 2SA1376.

ㄨ ⌊ ∂ ㄨ Ͻ я ￼ ˘ ῷ ᶾ Ͻ ٺ
General purpose amplifier applications requiring high breakdown voltages.

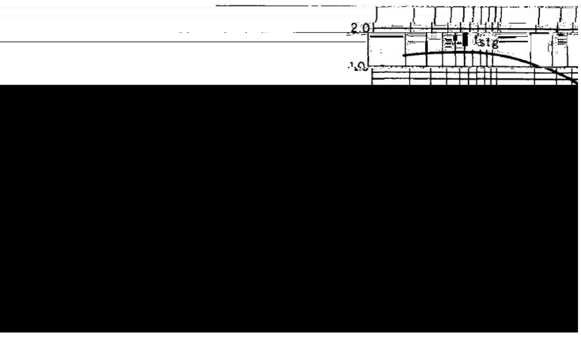
v ῼ Parameter	ɣ ᴺ Symbol	ῼӪ Rating	ᴅ Ꞡ Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	180	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Current – Continuous(Pulse)	I_{CP}	200	mA
Base Current - Continuous	I_B	20	mA
Collector Power Dissipation	P_C	750	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T		

/ Electrical Characteristic Curve

PT-Ta

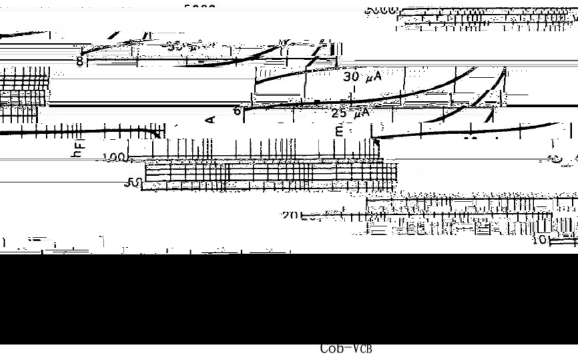


t-Ic

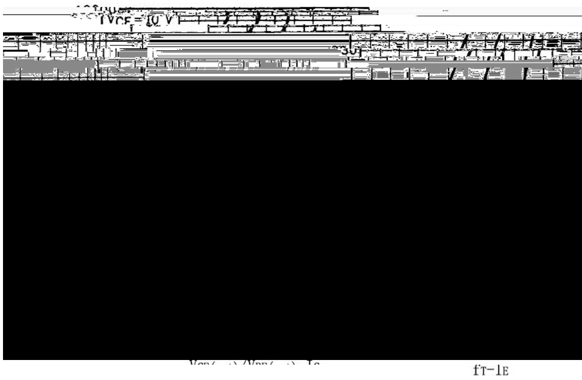


Ic-VCE

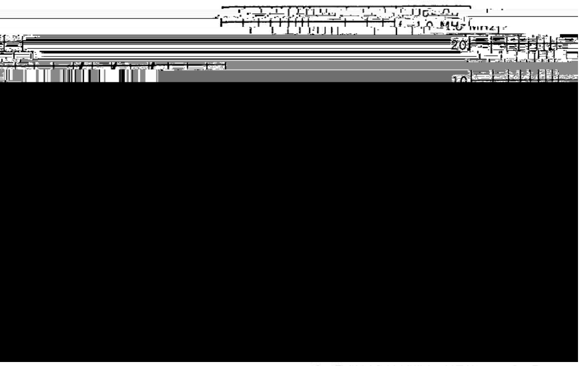
hFE-Ic



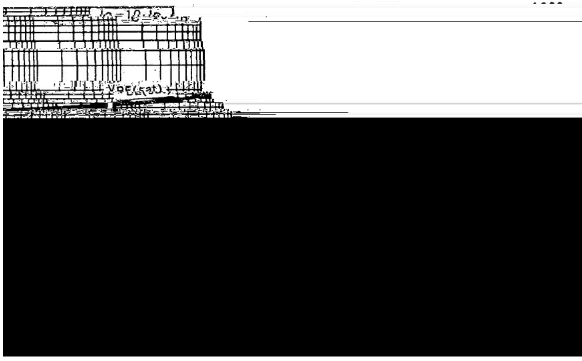
Ic-VBE



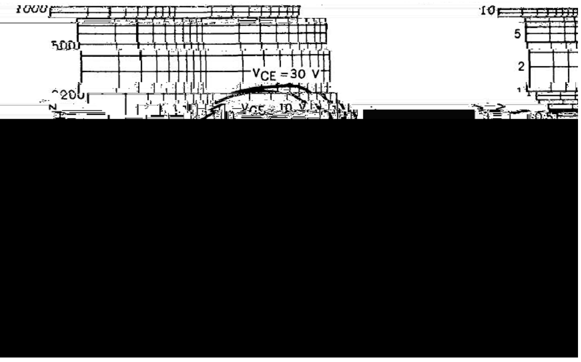
Cob-VCB



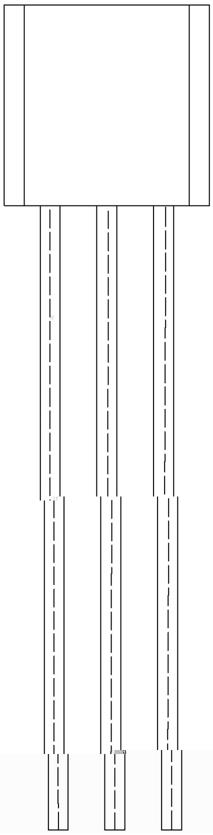
fT-IE



VCE(sat) / VBE(sat)-Ic



/ Marking Instructions



ب ˝ χ

EU꞊	ꟷ ʒ ᴎ Ꮘ
F67 : ; χ	ꟷ ʒ ᴺ Ꮘ
0꞊	ꟷ kɪʜ ˂ ⁶ Ꮘ
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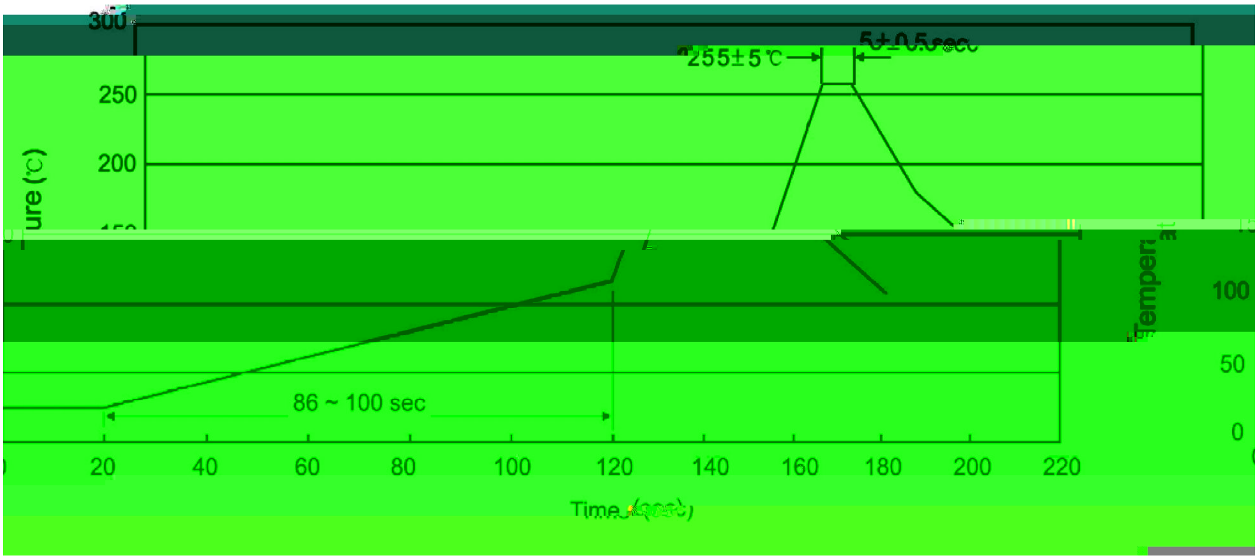
Note:

BR:	Company Code.
C3478:	Product Type.
0꞊	h_{FE} [illegible]

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ
1 ỉ ♬ □ ẙ 25 Ḱ 150 ɫ ı `H ڗ 60 Ḱ 90sec;
2 Ś Ӫ □ ẙ 255 ° 5 ɫ ı `H ڗ ʽY ʎ ʭ 5 ° 0.5sec;
3 ì ˙ Ɣ ˛ ɔ ھ ẙ ʭ 2 Ḱ 10 ɫ /sec.

Note:
1.Preheating:25~150 ɫ , Time:60~90sec.
2.Peak Temp.:255 ° 5 ɫ , Duration:5 ° 0.5sec.
3. Cooling Speed: 2~10 ɫ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ẙ χ 270 ° 5 ɫ `H ڗ χ 10 ° 1 sec.

Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

῝Ω ɽ ɣ Ŀ / BULK

Package Type	Units	Dimension	(unit mm3)